SiSH402DN

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Vishay Siliconix

RoHS

COMPLIANT

HALOGEN

FREE

N-Channel 30 V (D-S) MOSFET



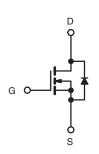
PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.0060					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 4.5 V	0.0080					
Q _g typ. (nC)	12					
I _D (A) ^{a, g}	35					
Configuration	Single					

FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- DC/DC converter
 - Notebook
 - POL



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH402DN-T1-GE3

ABSOLUTE MAXIMUM RATING	GS (T _A = 25 °C	, unless otherwise	noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	30	V	
Gate-source voltage		V _{GS}	± 20	v	
	T _C = 25 °C		35 ^{a, g}		
Continuous ducia compat (T. 150 °C)	T _C = 70 °C		35 ^g		
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	ID	19 ^{b, c}		
	T _A = 70 °C		15 ^{b, c}	— A	
Pulsed drain current		I _{DM}	70		
Avalanche current		I _{AS}	35		
Avalanche energy	L = 0.1 mH	E _{AS}	61	mJ	
Continuous source drain diada surrent	T _C = 25 °C	1	43		
Continuous source-drain diode current	T _A = 25 °C	I _S	3.2 ^{b, c}	— A	
	T _C = 25 °C		52		
Maximum power dissipation	T _C = 70 °C		33	14/	
	T _A = 25 °C	P _D	3.8 ^{b, c}	W	
	T _A = 70 °C		2 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stg} -55 to +150			
Soldering recommendations (peak temperature) ^{d, e}			260		

THEDMAL DESIGTANCE DATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R _{thJA}	24	33	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	1.9	2.4	0/10

Notes

a. Based on $T_C = 25 \ ^{\circ}C$

b. Surface mounted on 1" x 1" FR4 board

t = 10 s c.

c. t = 10 s
d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
f. Maximum under steady state conditions is 81 °C/W

Package limited

g.

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Document Number: 75897

For technical questions, contact: pmostechsupport@vishay.com

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	30	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	24	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-6	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1.15	-	2.2	V	
Gate-source leakage	I_{GSS} $V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zara gata valtaga drain avreat		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	-	-	5		
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	50	-	-	А	
	D	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 19 \text{ A}$	-	0.0048	0.0060	0	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 16.6 \text{ A}$	-	0.0064	0.0080	Ω	
Forward transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 19 \text{ A}$	-	82	-	S	
Dynamic ^b	•						
Input capacitance	C _{iss}		-	1700	-		
Output capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	350	-	pF	
Reverse transfer capacitance	C _{rss}		-	140	-		
	0	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 19 \text{ A}$	-	28	42		
Total gate charge	Qg		-	12	21		
Gate-source charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 19 \text{ A}$ $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		5.4	-	nC	
Gate-drain charge	Q _{gd}		-	4.6	-		
Gate resistance	Rg	f = 1 MHz	-	1.2	2.4	Ω	
Turn-on delay time	t _{d(on)}		-	25	40		
Rise time	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_{L} = 1.5 \Omega$	-	20	30		
Turn-off delay time	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	25	40		
Fall time	t _f		-	15	25		
Turn-on delay time	t _{d(on)}		-	12	20	ns	
Rise time	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_{L} = 1.5 \Omega$	-	10	15		
Turn-off delay time	t _{d(off)}	$I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	25	40	1	
Fall time	t _f		-	10	15		
Drain-Source Body Diode Characteristi	cs						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	30	٨	
Pulse diode forward current	I _{SM}		-	-	70	A	
Body diode voltage	V _{SD}	$I_{\rm S} = 10$ A, $V_{\rm GS} = 0$ V	-	0.8	1.2	V	
Body diode reverse recovery time	t _{rr}		-	25	50	ns	
Body diode reverse recovery charge	Q _{rr}	I _F = 10 A, di/dt = 100 A/μs,	-	17	35	nC	
Reverse recovery fall time	t _a	$T_J = 25 \ ^{\circ}C$	-	13	-		
Reverse recovery rise time	t _b		-	12	-	ns	

Notes

a. Pulse test: pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing

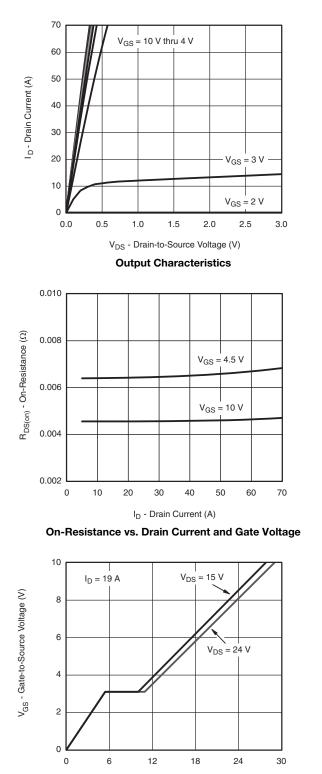
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



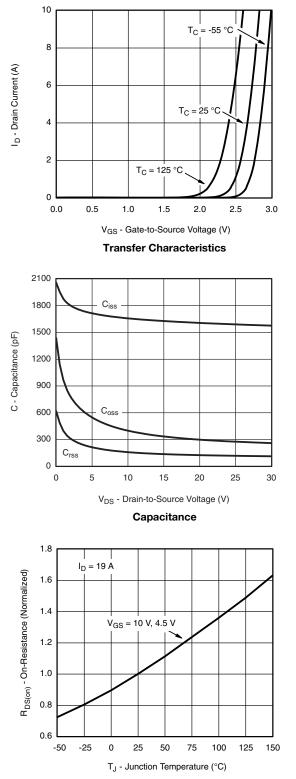
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Qg - Total Gate Charge (nC)

Gate Charge



On-Resistance vs. Junction Temperature

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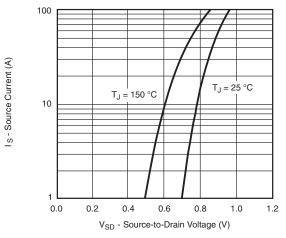
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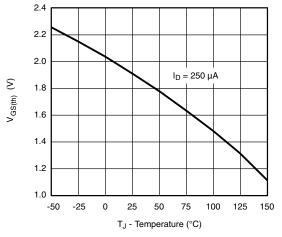
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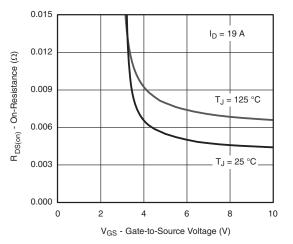
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



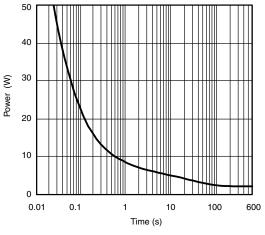
Source-Drain Diode Forward Voltage



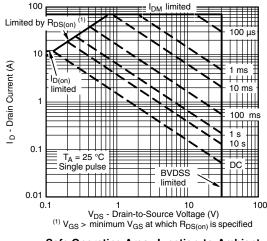
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)



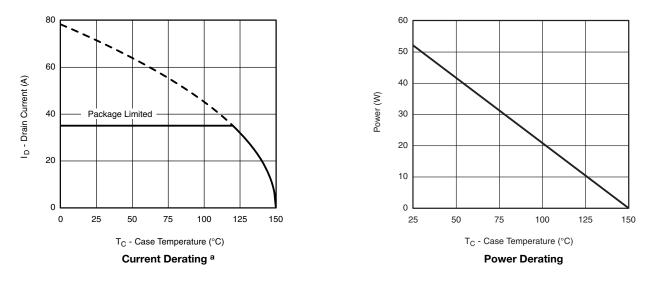
Safe Operating Area, Junction-to-Ambient



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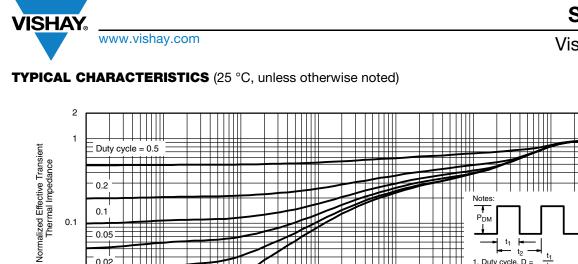
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



┼┼

0.1

0.05

0.02

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10⁻³

Single pulse

0.1

0.01 10-4

10-2 10-1 10 1

PDM

t₁

1. Duty cycle, D =

4. Surface mounted

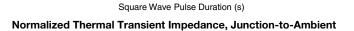
t₂

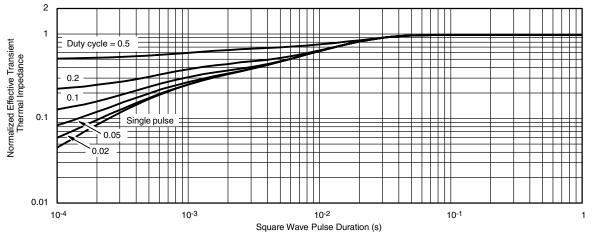
2. Per unit base = RthJA = 65 °C/W 3. T_{JM} - $T_A = P_{DM}Z_{thJA}^{(t)}$

t₁ t₂

100

600





Normalized Thermal Transient Impedance, Junction-to-Case

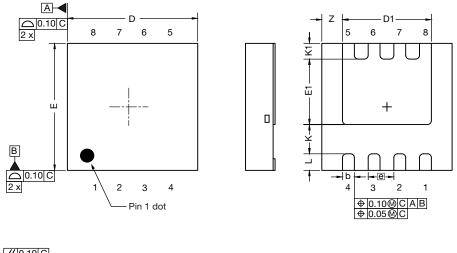
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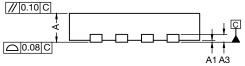
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Case Outline for PowerPAK[®] 1212-SWLH and PowerPAK[®] 1212-8SH





		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	0.82	0.90	0.98	0.032	0.035	0.038	
A1	0.00	-	0.05	0.000	-	0.002	
A3		0.20 ref.	•		0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.15	2.25	2.35	0.085	0.089	0.093	
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	1.60	1.70	1.80	0.063	0.067	0.071	
е		0.65 bsc.			0.026 bsc.		
К	0.76 ref.				0.030 ref.		
K1	0.41 ref.			0.41 ref. 0.016 ref.			
L	0.33	0.43	0.53	0.013	0.017	0.021	
Z	0.525 ref.			5 ref. 0.021 ref.			

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RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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